

# NE57810

## Advanced DDR memory termination power with external reference voltage in

Rev. 04 — 24 November 2008

Product data sheet

## 1. Introduction

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The NE57810 is designed to provide power for termination of a Double Data Rate (DDR) SDRAM memory bus. It significantly reduces parts count, board space, and overall system cost compared to previous solutions.

## 2. General description

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The NE57810 DDR termination regulator maintains an output voltage (DDR reference bus voltage) that is half the RAM supply voltage. It is capable of providing up to  $\pm 3.5$  A for sustained periods. Overcurrent limiting protects the NE57810 from inrush currents at start-up. Overtemperature shutdown protects the device in extreme temperature situations.

The package is thermally robust for flexibility of thermal design. The NE57810 is a linear regulator so no external inductors or switching FETs are necessary. Fast response to load changes reduces the need for output capacitors.

## 3. Features

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- Fast transient response time
- Overtemperature protection
- Overcurrent protection
- Commercial (0 °C to +70 °C) temperature range
- Reduced need for external components (switching FETs, inductors, decoupling capacitors)
- Internal divider maintains termination voltage at half the memory supply voltage
- Reference out for other memory and control components
- Optional external voltage reference in for flexible application
- Compatible with DDR-I ( $V_{DD} = 2.5$  V) or DDR-II ( $V_{DD} = 1.8$  V) SDRAM systems

## 4. Applications

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- Desktop microcomputer systems
- Workstations
- Servers
- Game machines
- Set top boxes
- Embedded systems

■ Digital video recorders

## 5. Ordering information

Table 1. Ordering information

| Type number | Package |   | Version |
|-------------|---------|---|---------|
|             | Name    | Description   |         |
| NE57810S    | -       | plastic single-ended surface-mounted package; 5 leads | SOT756  |

## 6. Functional diagram

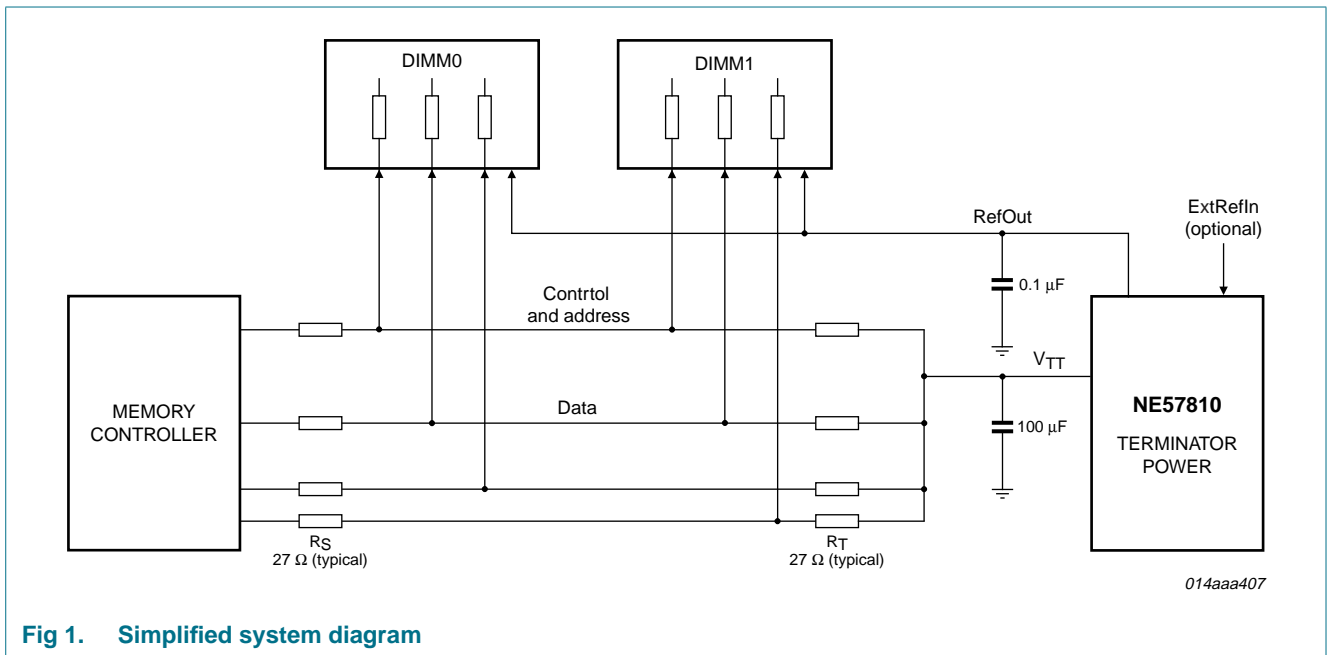


Fig 1. Simplified system diagram

## 7. Pinning information

### 7.1 Pinning

Table 2. Pinning

| Symbol   | Pin | Description                   | Simplified outline |
|----------|-----|-------------------------------|--------------------|
| $V_{TT}$ | 1   | Regulated terminator voltage  |                    |
| $V_{DD}$ | 2   | Power supply                  |                    |
| $V_{SS}$ | 3   | Circuit ground <sup>[1]</sup> |                    |
| ExtRefIn | 4   | External reference voltage in |                    |
| RefOut   | 5   | Reference voltage out         |                    |

[1] The thermal pad on the rear of the device (shown by dotted outline) is connected electrically to  $V_{SS}$  internally and provides enhancement to thermal conductivity. It should not be used as the primary connection to ground as device specifications indicate the use of the  $V_{SS}$  pin for this purpose.

## 8. Application design-in information

The NE57810 can be used in a variety of DDR memory configurations. Its small footprint, fast transient response and reduced need for large bulk output capacitance, makes it highly adaptable. Some of examples methods of use are described in the following sections.

### 8.1 Normal operating mode ( $V_{TT} = V_{DDR}/2$ )

The most common implementation of a DDR terminator regulator using the NE57810 is shown in [Figure 2](#). The NE57810 has an internal resistor divider between the  $V_{DD}$  (pin 2) and  $V_{SS}$  (pin 3) pins which maintains the output voltage,  $V_{TT}$ , at  $V_{DD}/2$ .

Typically, the  $V_{DD}$  voltage is the DDR RAM supply voltage, which can range from 1.8 V to 2.5 V. The center node of this resistor divider is connected to ExtRefIn (pin 4). This node acts as the reference for the  $V_{TT}$  output voltage and the buffered RefOut signal (pin 5).

If the ExtRefIn pin is not connected to other voltage sources, two small bypass capacitors (0.01  $\mu\text{F}$ ) should be placed between the ExtRefIn pin and the  $V_{SS}$  and  $V_{DD}$  pins to improve the terminator's noise performance. These two capacitors improve enable the terminator to better track any variations in the memory  $V_{DD}$  voltage. This method can be seen in [Figure 2](#).

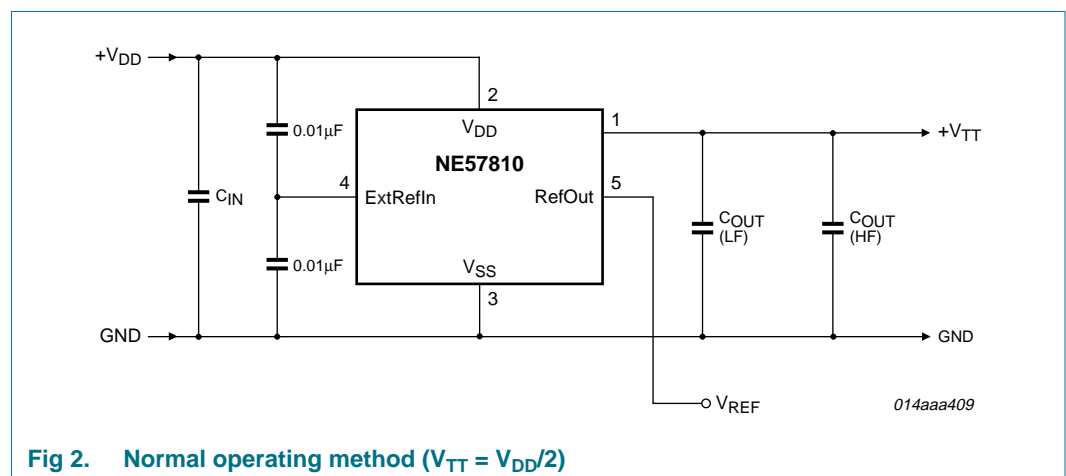


Fig 2. Normal operating method ( $V_{TT} = V_{DD}/2$ )

There are two components to the memory signal load: a high frequency component caused by the 266 MHz plus speed of the address, data and control buses, and a low frequency component caused by the time-average skew of all of the bus states away from an equal number of 1s and 0s. Electrolytic and tantalum capacitors show inductance at the high frequencies, so two types of capacitors are required for output filtering.

A very good, low ESR bulk electrolytic capacitor of no less than 470  $\mu\text{F}$  should be placed next to the terminator which, in turn, should be placed as close as possible to the memory array. Multiple high frequency ceramic filter capacitors are also needed for high speed transient filtering and output stability. These capacitors may be from  $V_{TT}$  to  $V_{SS}$  (shown in the diagrams) or one half from  $V_{TT}$  to  $V_{DD}$  and the other half from  $V_{TT}$  to  $V_{SS}$  so the output will better track any variations in the  $V_{DD}$  voltage.

For different memory sizes, the values of the recommended output filter capacitances will change. For a 256 MB memory space, for example, approximately 100  $\mu\text{F}$  of ceramic surface mount chip capacitors should be evenly distributed across the physical memory layout. Depending upon the PCB noise environment, this can be 10 pieces of 10  $\mu\text{F}$ , 20 pieces of 5  $\mu\text{F}$ , and so on.

### 8.2 Externally programmed $V_{\text{TT}}$ output voltage

The NE57810 enables use of an external reference voltage to set its  $V_{\text{TT}}$  output voltage. This pin (ExtRefIn pin 4) is used for applications where the  $V_{\text{TT}}$  voltage is not  $V_{\text{DD}}$  divided by 2. This allows  $V_{\text{TT}}$  voltage and current to be drawn from a power supply bus that is not the DDR RAM supply voltage. This has some advantages when you are attempting to better match the power being drawn from the outputs emerging from the main system power supply. This can be seen in [Figure 3](#).

The internal reference voltage is set by two matched 100 k $\Omega$  resistors connected in a resistor divider between the  $V_{\text{DD}}$  and  $V_{\text{SS}}$  pins of the NE57810

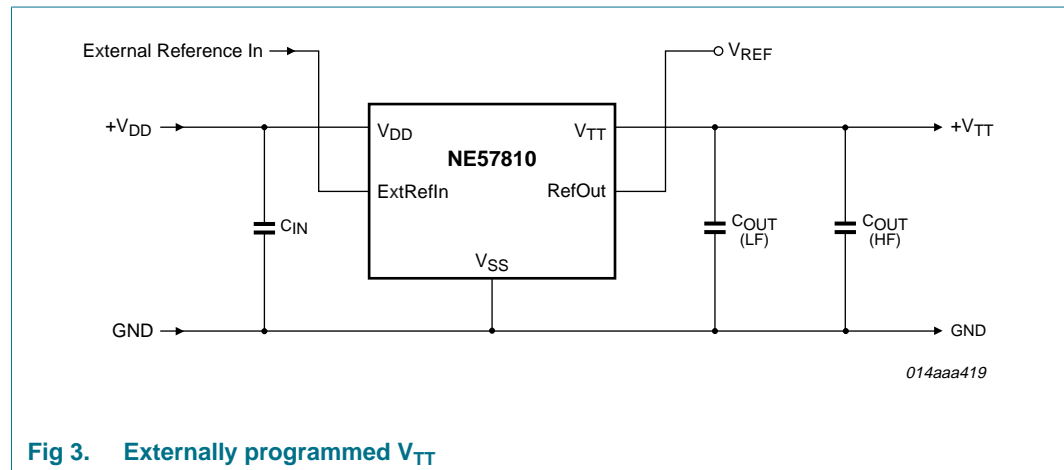


Fig 3. Externally programmed  $V_{\text{TT}}$

### 8.3 Cascading the NE57810

For high-performance computer systems, sometimes memory banks are driven 180 degrees out of phase with one another in such a way that the apparent access time is halved (even and odd memory addresses). To do this, NXP recommends that two NE57810s are used, one to terminate each memory bank.

Cascading NE57810 terminators offers two advantages, it improves the system noise performance by bringing the memory SIMMs closer to the terminator, and it distributes any heat generated by the terminator system. By using the RefOut pin from one NE57810 to the ExtRefIn pin for the other NE57810(s) used in the system, one can always guarantee that the  $V_{\text{TT}}$  voltages are identical.

Because of the very tight output voltage regulation of the NE57810, the  $V_{\text{TT}}$  outputs should never be wired together. This is because the terminators would 'fight' one another if their output were different by only a few millivolts. This method can be used in either the normal operating mode and the externally programmed operating mode. This method of use can be seen in [Figure 4](#).

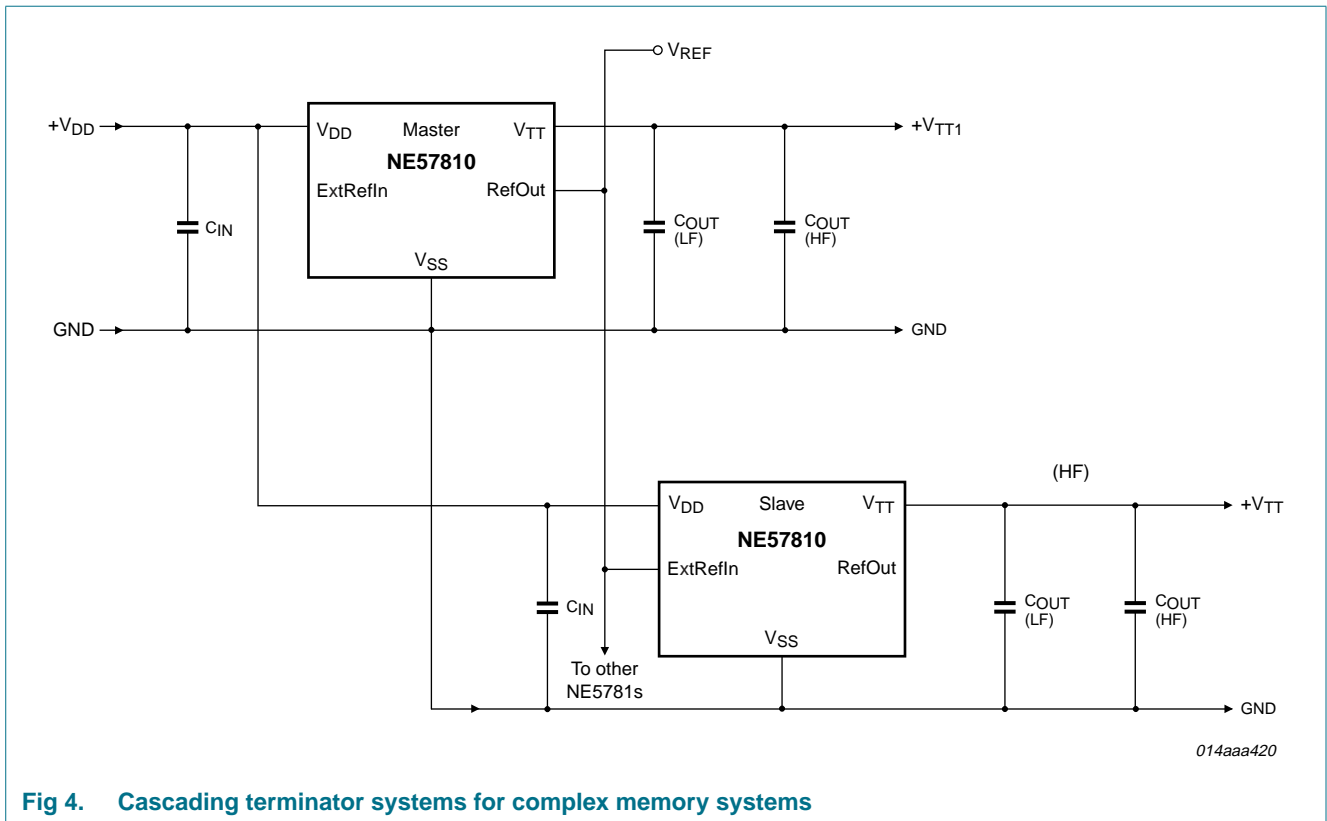


Fig 4. Cascading terminator systems for complex memory systems

## 9. Technical description

The NE57810 supplies power to the DDR memory bus termination resistors at nominally half the voltage supplied to the memory ICs or DIMMs. DDR memory output drivers source and sink current into and out of their outputs.

A typical DDR memory system is seen in [Figure 1](#). Each input/output pin on the bus has a series 20 Ω resistor connected to it. The bus is terminated to the DDR terminator through a 27 Ω to 50 Ω resistance. The memory system then requires current from the V<sub>TT</sub> terminator bus only when the instantaneous values of the aggregate bus state are not equal amounts of 1s and 0s.

When memory bus speeds are in the 200 MHz to 300 MHz region, the period of any single bus state is extremely small. This permits the DDR bus termination regulator to be a linear power operational amplifier that can source and sink current instantly to the DDR bus from the V<sub>DD</sub> supply voltage.

[Figure 6](#) models the V<sub>TT</sub> loading condition of each bus line equivalent circuit during operation and with terminating resistors.

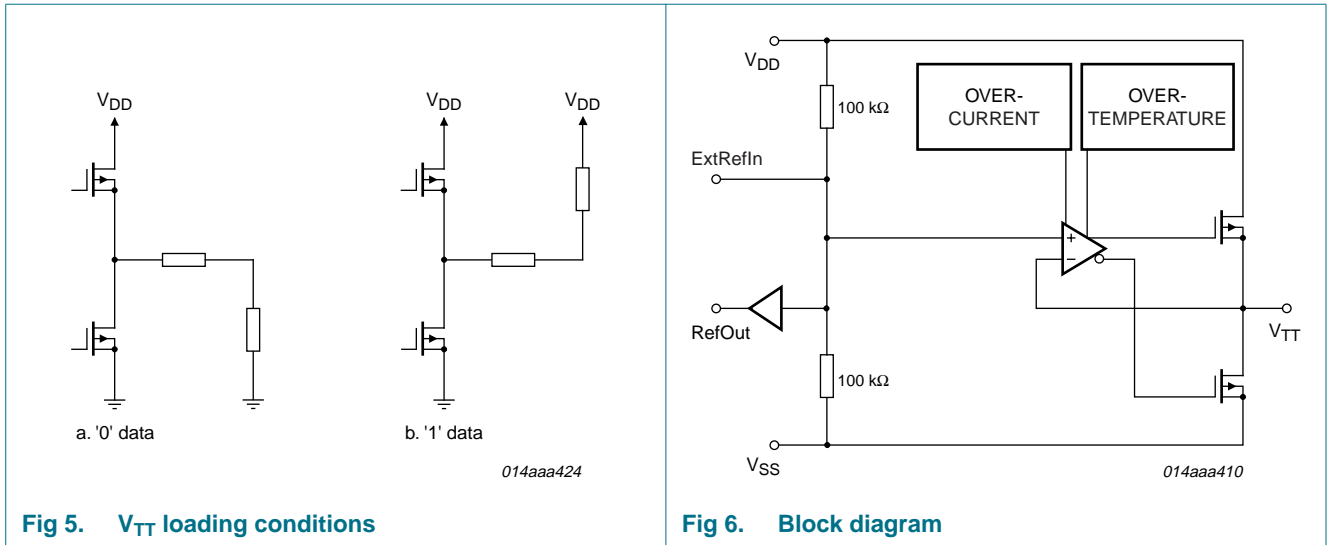


Fig 5. V<sub>TT</sub> loading conditions

Fig 6. Block diagram

This yields the worst case current loading [Equation 1](#):

$$I_{O(max)} = \frac{N_{DDR} V_{DD}}{2(R_T + R_S)} \tag{1}$$

Where:

- N<sub>DDR</sub> is the total number of terminated control, address and data lines within the DDR memory system. (typically 192).
- R<sub>T</sub> is the value of the terminating resistors.
- R<sub>S</sub> is the value of the series resistors from the active output driver.

Hence the worst case current loading condition, where there are either all 1s or all 0s for an instant, and R<sub>T</sub> is 27 Ω and R<sub>S</sub> is 20 Ω, produces an instantaneous output current of either +3.5 A or -3.5 A.

## 10. Thermal design

Designing the proper thermal system for the NE57810 is important for its reliable operation. The NE57810 will be operating at an average power level less than the maximum rating of the part. In a typical DDR terminator system the average power dissipation is between 0.8 W and 1.5 W.

The termination power will vary as the average number of 1s and 0s changes during normal operation of the DDR memory. The load current will assume a new value for each bus cycle at a 266 MHz rate, and will increase and decrease as the statistical average of bus states change.

The terminator heat sink must be designed to accommodate the average power as a steady state condition and be able to withstand momentary periods of increased dissipation, typically 2 seconds to 5 seconds duration. For the typical NE57810 application, the power dissipated by the terminator can be calculated by [Equation 2](#):

$$P_D = I_{DD} \times V_{TT} W \tag{2}$$

The thermal resistance of a surface mount package is given as  $R_{th(j-a)}$ , the thermal resistance from the junction to air. JESD51-7 specifies a 4-layer multilayer PCB (2 oz/1 oz/1 oz/2 oz copper) that is 4 inches on each side.

This is probably the best (or lowest) thermal resistance you will see in any application. Most applications cannot afford the PCB area to create this situation, but the thermal performance of a multilayer PCB will still provide a significant heatsinking effect. The actual thermal resistance will be higher than the 16.5 °C/W given for the 4-layer JEDEC PCB.

Figure 7 shows the thermal resistance you can expect for heatsinking PCB areas less than the JEDEC specification. The graph is for a 2 oz single-sided PCB with a square area of the side dimension as given on the X-axis. If you use a double-sided PCB with some plated-through holes to help transfer heat to the bottom side, the thermal resistance only improves by about 3 °C/W to 4 °C/W.

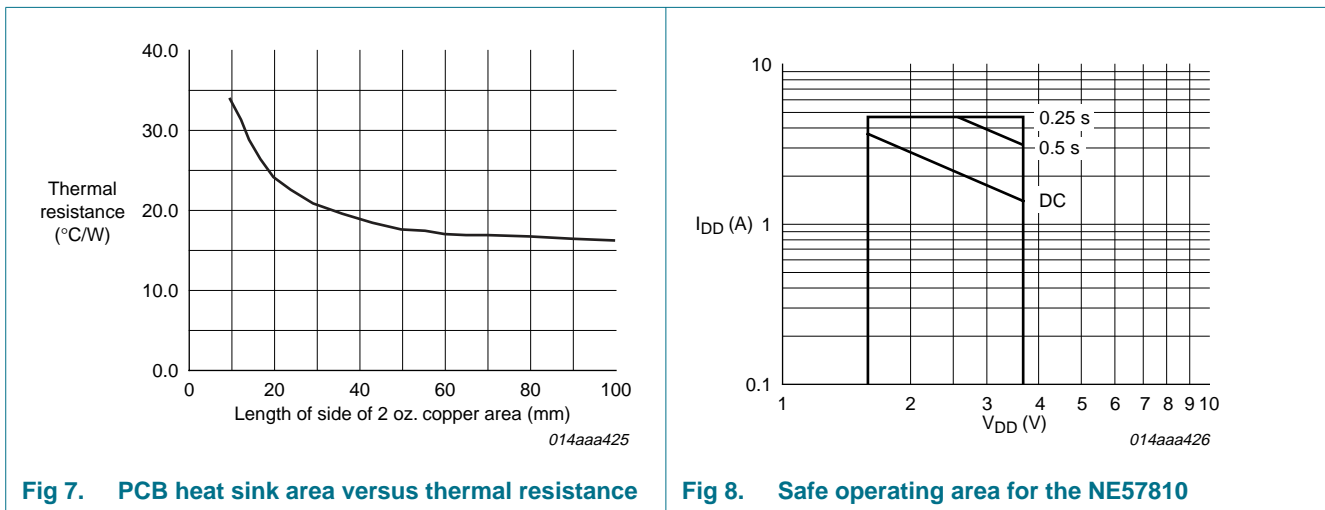


Fig 7. PCB heat sink area versus thermal resistance

Fig 8. Safe operating area for the NE57810

After the power is estimated, the minimum PCB area can be determined by calculating the worst case thermal resistance and, based on Figure 7, determine the PCB area. This is done by Equation 3:

$$R_{qJA(\min)} = \frac{T_j - T_{amb}}{P_D} \tag{3}$$

Where:

- $T_j$  is the maximum desired junction temperature.
- $T_{amb}$  is the highest expected local ambient temperature.
- $P_D$  is the estimated average power

The junction temperature should be kept well away from the overtemperature cut-off threshold temperature (+150 °C) in normal operation. Using the above power dissipation, the highest ambient temperature and a junction temperature of +125 °C, calculate the maximum thermal resistance using Equation 4, (1.5 W is used only as an example).

$$R_{th((j-a)(\min))} = \frac{125^\circ C - 70^\circ C}{1.5W} = 36.6^\circ C/W \tag{4}$$

Looking at [Figure 7](#), you see that this power dissipation requires a minimum PCB island area of 225 mm<sup>2</sup> (15 mm on each side). This is the smallest area you could use at this power dissipation. Of course, increasing this area will allow the NE57810 to operate at cooler temperatures, thus enhancing its long-term reliability.

## 11. Limiting values

**Table 3. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter            | Conditions                                 | Min  | Max  | Unit |
|------------------|----------------------|--|------|------|------|
| V <sub>DD</sub>  | supply voltage       | V <sub>DD</sub> to V <sub>SS</sub> voltage | -0.3 | +3.6 | V    |
| T <sub>amb</sub> | ambient temperature  |  | 0    | +70  | °C   |
| T <sub>stg</sub> | storage temperature  |  | -40  | +165 | °C   |
| T <sub>j</sub>   | junction temperature |  | -    | 160  | °C   |
| P <sub>D</sub>   | power dissipation    | [1]  | -    | 3.3  | W    |

[1] Tested on a minimum footprint on a four-layer PCB per JEDEC specification JESD51-7

## 12. Thermal characteristics

**Table 4. Thermal characteristics**

| Symbol               | Parameter                                   | Conditions | Typ  | Unit |
|----------------------|---|------------|------|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient |            | 16.5 | °C/W |

## 13. Characteristics

**Table 5. Characteristics**

T<sub>amb</sub> = 0 °C to +70 °C, V<sub>DD</sub> = 2.5 V; I<sub>TT</sub> = -3.5 A to +3.5 A, unless otherwise specified.

| Symbol            | Parameter               | Conditions                      | Min  | Typ                | Max  | Unit |
|-------------------|-------------------------|---------------------------------|------|--------------------|------|------|
| V <sub>TT</sub>   | output voltage          | ExtRefIn not connected          | -    | V <sub>DD</sub> /2 | -    | V    |
| V <sub>ACC</sub>  | output voltage accuracy | [1]                             | -15  | -                  | +15  | mV   |
| V <sub>DD</sub>   | supply voltage          |                                 | 1.6  | -                  | 3.6  | V    |
| I <sub>Q</sub>    | supply current          | I <sub>TT</sub> = 0 A           | -    | 14                 | 30   | mA   |
| I <sub>TT</sub>   | output current          | 2.5 V ≤ V <sub>DD</sub> ≤ 3.6 V | -3.5 | -                  | +3.5 | A    |
|                   |                         | V <sub>DD</sub> = 1.6 V         | -2.5 | -                  | +2.5 | A    |
| ΔV <sub>TT</sub>  | load regulation         | I <sub>TT</sub> = ± 1.0 A       | -    | ±6                 | -    | mV   |
|                   |                         | I <sub>TT</sub> = ± 3.5 A       | -18  | -                  | +18  | mV   |
| C <sub>LOAD</sub> | load capacitance        | stable operation                | [2]  | 100                | -    | μF   |

### External reference in

|                           |                         |  |     |     |                       |     |
|---------------------------|-------------------------|--|-----|-----|-----------------------|-----|
| V <sub>TT</sub>           | output voltage swing    |  | 0.8 | -   | V <sub>DD</sub> - 0.8 | V   |
| R <sub>in(ExtRefIn)</sub> | input impedance         |  | 35  | 50  | -                     | kΩ  |
|                           | output voltage accuracy | I <sub>TT</sub> = 0 A                                | [3] | -15 | -                     | +15 |
|                           | line regulation         | ExtRefIn = 1.25 V;<br>V <sub>DD</sub> = 2.25 - 3.6 V | -6  | -   | +6                    | mV  |



**Table 5. Characteristics ...continued** $T_{amb} = 0^{\circ}\text{C}$  to  $+70^{\circ}\text{C}$ ,  $V_{DD} = 2.5\text{ V}$ ;  $I_{TT} = -3.5\text{ A}$  to  $+3.5\text{ A}$ , unless otherwise specified.

| Symbol               | Parameter                       | Conditions                       | Min     | Typ      | Max | Unit |
|----------------------|---------------------------------|----------------------------------|---------|----------|-----|------|
| <b>Reference out</b> |                                 |                                  |         |          |     |      |
| RefOut               | voltage reference out           | IrefOut = 0 A;<br>source or sink | [4] -15 | ExtRefIn | +15 | mV   |
| IrefOut              | reference out current max       |                                  | 2.2     | 3        | -   | mA   |
| C <sub>LOAD</sub>    | load capacitance                | stable operation                 | 0.1     | -        | -   | μF   |
| <b>Power stage</b>   |                                 |                                  |         |          |     |      |
| I <sub>lim</sub>     | current limit                   |                                  | 3.6     | 4.5      | 6.5 | A    |
| T <sub>lim</sub>     | temperature shutdown            |                                  | -       | 150      | -   | °C   |
|                      | temperature shutdown hysteresis |                                  | -       | 20       | -   | °C   |

[1]  $V_{ACC} = V_{TT} - V_{DD}/2$ .

[2] Ceramic capacitors only. Low ESR electrolytic capacitors are not necessary.

[3] Voltage accuracy refers to voltage at ExtRefIn pin.

[4] RefOut voltage referenced to  $0.5 V_{DD}$  if ExtRefIn is not connected.

## 14. Typical performance curves

[Figure 9](#) through [Figure 13](#) show the typical performance curves for the NE57810.

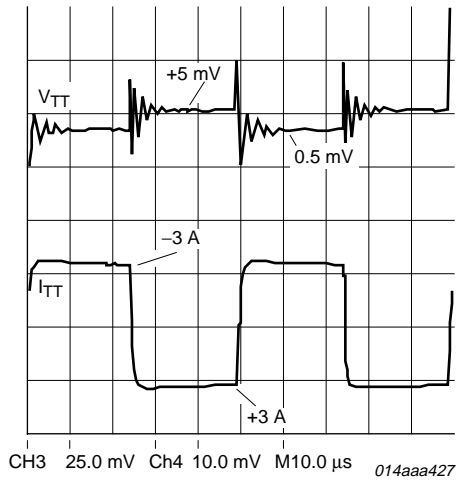


Fig 9.  $V_{TT}$  transient response (output filter 50  $\mu$ F ceramic)

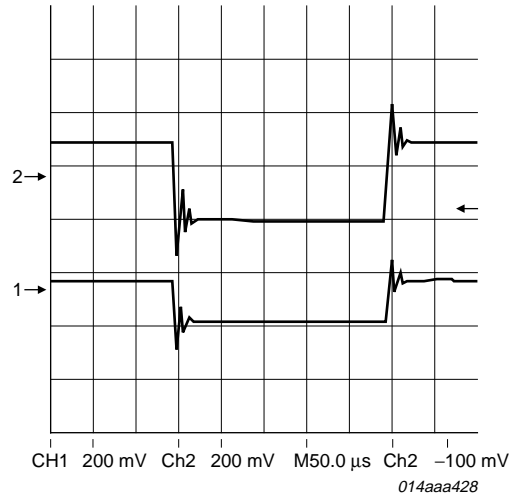


Fig 10.  $V_{DD}$  to  $V_{TT}$  response (output filter 50  $\mu$ F ceramic)

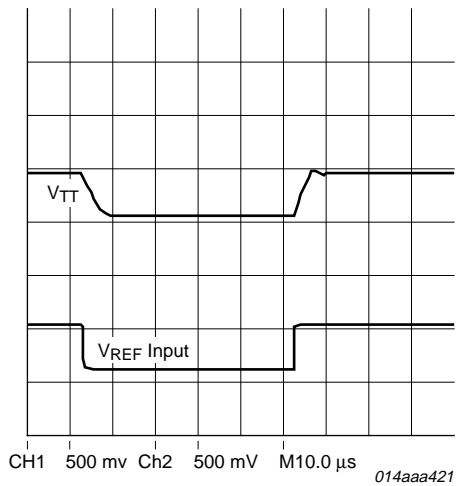


Fig 11.  $V_{REF}$  to  $V_{TT}$  transient response (output filter 820  $\mu$ F + 50  $\mu$ F ceramic)

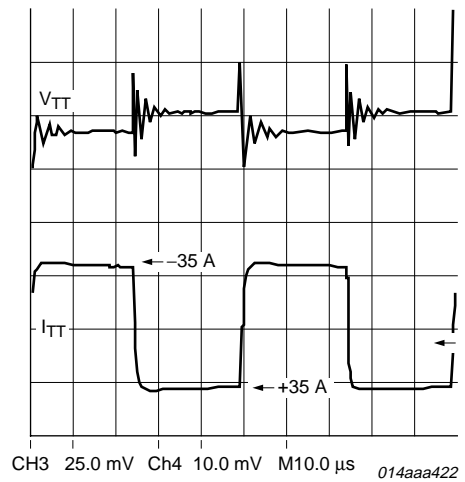


Fig 12.  $V_{REF}$  to  $V_{TT}$  transient response (output filter 50  $\mu$ F ceramic)

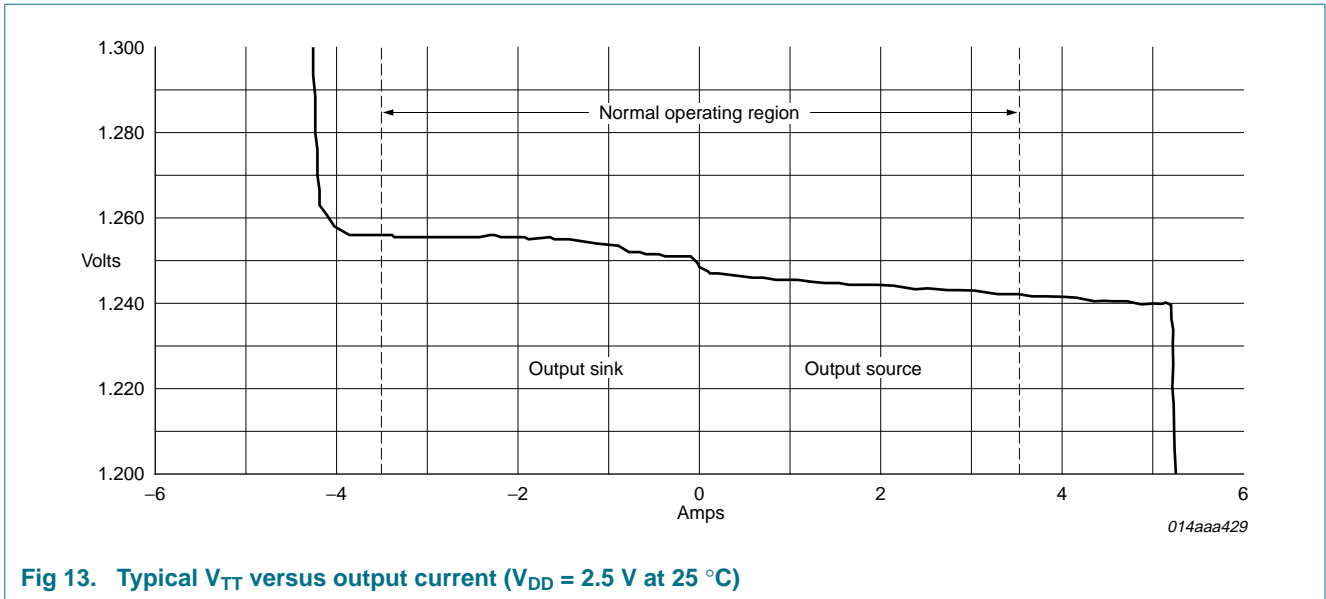
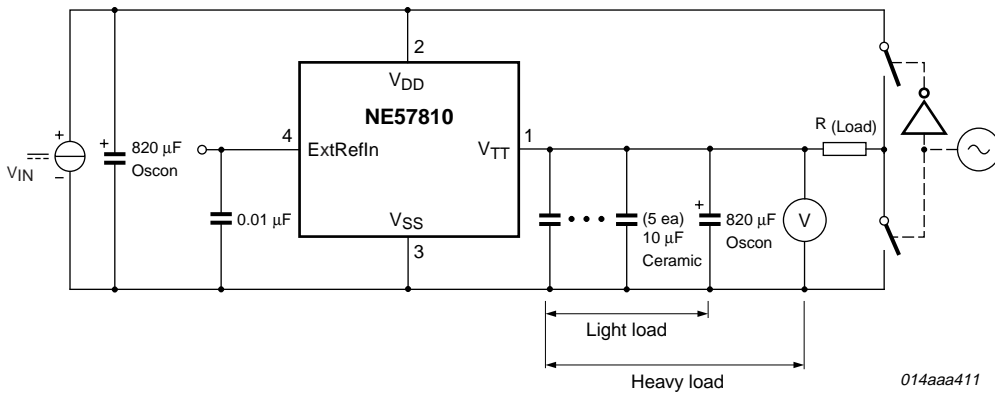


Fig 13. Typical  $V_{TT}$  versus output current ( $V_{DD} = 2.5\text{ V}$  at  $25\text{ °C}$ )

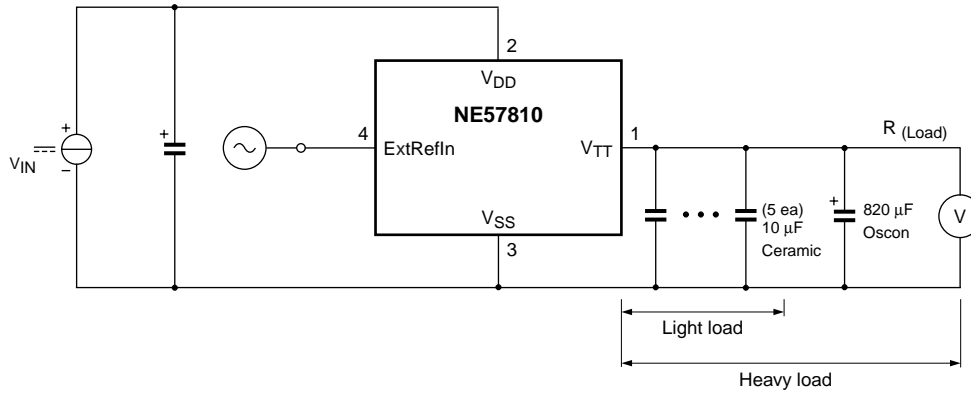
## 15. Test information

[Figure 14](#), [Figure 15](#) and [Figure 16](#) show the diagrams for the NE57810 test circuits.



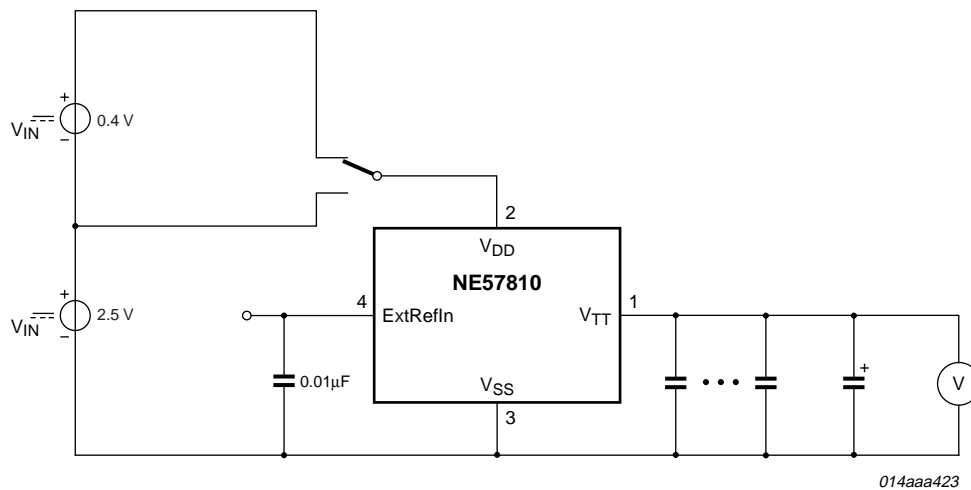
014aaa411

Fig 14. Load transient test (+3 A to -3 A)



014aaa412

Fig 15. ExtRefIn to VTT transient test



014aaa423

Fig 16. VDD to VTT transient test

16. Package outline

Plastic single-ended surface-mounted package; 5 leads

SOT756

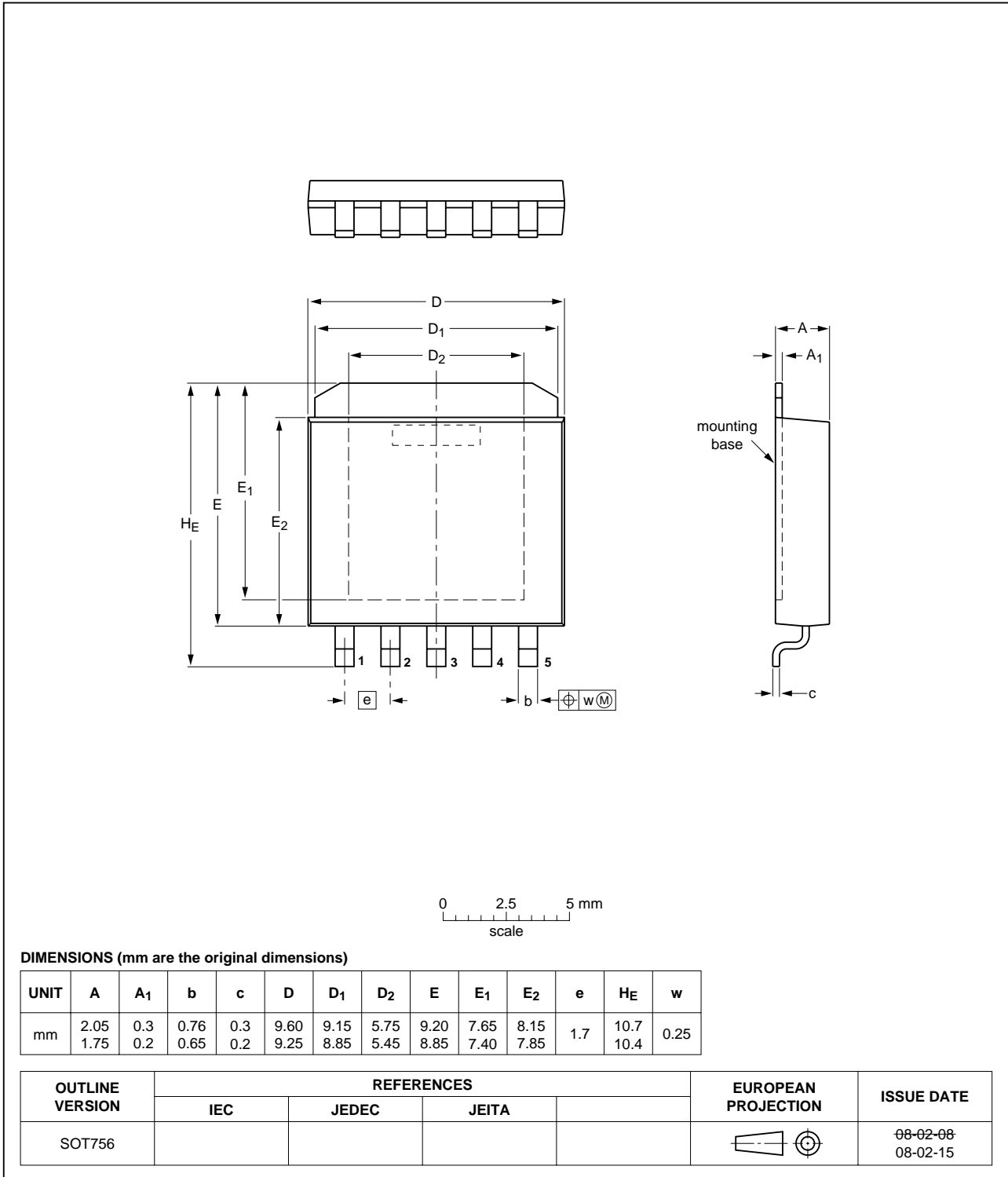


Fig 17. Package outline SOT756

## 17. Revision history

Table 6. Revision history

| Document ID    | Release date  | Data sheet status  | Change notice | Supersedes |
|----------------|---|--------------------|---------------|------------|
| NE57810_4      | 20081124  | Product data sheet | -             | NE57810_3  |
| Modifications: | • The values for $I_{lim}$ in <a href="#">Table 5</a> has been updated. |                    |               |            |
| NE57810_3      | 20080702  | Product data sheet | -             | NE57810_2  |
| NE57810_2      | 20030912  | Product data sheet | -             | NE57810_1  |
| NE57810_1      | 20020716  | Product data sheet | -             | -          |

## 18. Legal information

### 18.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition  |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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## 20. Contents

|           |  |           |
|-----------|--|-----------|
| <b>1</b>  | <b>Introduction</b> .....                            | <b>1</b>  |
| <b>2</b>  | <b>General description</b> .....                     | <b>1</b>  |
| <b>3</b>  | <b>Features</b> .....                                | <b>1</b>  |
| <b>4</b>  | <b>Applications</b> .....                            | <b>1</b>  |
| <b>5</b>  | <b>Ordering information</b> .....                    | <b>2</b>  |
| <b>6</b>  | <b>Functional diagram</b> .....                      | <b>2</b>  |
| <b>7</b>  | <b>Pinning information</b> .....                     | <b>2</b>  |
| 7.1       | Pinning .....  | 2         |
| <b>8</b>  | <b>Application design-in information</b> .....       | <b>3</b>  |
| 8.1       | Normal operating mode ( $V_{TT} = V_{DDR}/2$ ) ..... | 3         |
| 8.2       | Externally programmed $V_{TT}$ output voltage ...    | 4         |
| 8.3       | Cascading the NE57810 .....                          | 4         |
| <b>9</b>  | <b>Technical description</b> .....                   | <b>5</b>  |
| <b>10</b> | <b>Thermal design</b> .....                          | <b>6</b>  |
| <b>11</b> | <b>Limiting values</b> .....                         | <b>8</b>  |
| <b>12</b> | <b>Thermal characteristics</b> .....                 | <b>8</b>  |
| <b>13</b> | <b>Characteristics</b> .....                         | <b>8</b>  |
| <b>14</b> | <b>Typical performance curves</b> .....              | <b>9</b>  |
| <b>15</b> | <b>Test information</b> .....                        | <b>11</b> |
| <b>16</b> | <b>Package outline</b> .....                         | <b>13</b> |
| <b>17</b> | <b>Revision history</b> .....                        | <b>14</b> |
| <b>18</b> | <b>Legal information</b> .....                       | <b>15</b> |
| 18.1      | Data sheet status .....                              | 15        |
| 18.2      | Definitions .....                                    | 15        |
| 18.3      | Disclaimers .....                                    | 15        |
| 18.4      | Trademarks .....                                     | 15        |
| <b>19</b> | <b>Contact information</b> .....                     | <b>15</b> |
| <b>20</b> | <b>Contents</b> .....                                | <b>16</b> |

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For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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